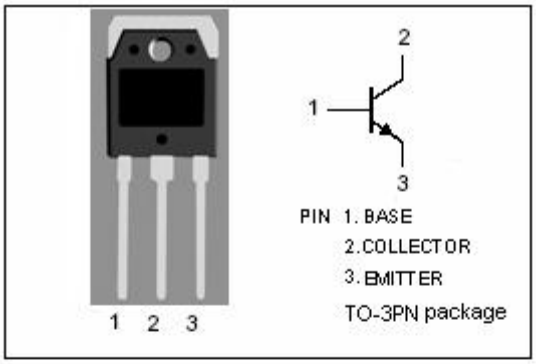
isc Silicon NPN Power Transistor — 2N6935

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 400V(Min)
- High Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

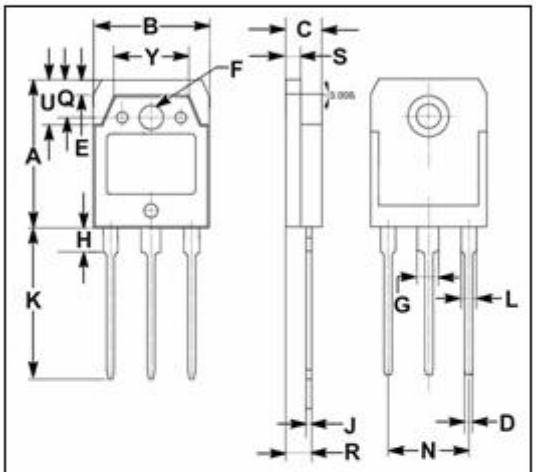
- Designed for off-line power supplies，switching regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	650	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base voltage	8	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	23	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ T_C=25℃	175	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	0.71	℃/W



DIM	mm MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	650			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; R_{BE}= ∞	400			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1m A; I_C= 0	8			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 15A; I_B= 3.0A			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 15A; I_B= 3.0A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 650V ; I_E= 0			100	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= 8V; I_C= 0			100	μ A
h_{FE}	DC Current Gain	I_C= 15A ; V_{CE}= 3V	8		35	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test}= 1.0MHz	150			pF
Switching Times						
t_d	Delay Time	I_C= 15A, I_{B1}= -I_{B2}= 3A R_L= 20 Ω ; V_{CC}= 300V			0.1	μ s
T_r	Rise Time				0.7	μ s
t_{stg}	Storage Time				2.5	μ s
t_f	Fall Time				0.5	μ s

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